

L Number	Hits	Search Text	DB	Time stamp
1	1	5108939.pn. and flash BEST AVAILABLE COPY	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:53
2	0	6160287.pn. and nonvolatile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:53
-	224	(nonvolatile adj memory adj cell) and (floating adj gate) and spacer and (control adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 11:25
-	2	(nonvolatile adj memory adj cell) and (main adj floating adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:54
-	3	(nonvolatile adj memory adj cell) and (connecting adj floating adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/03 11:28
-	296	(nonvolatile adj memory adj cell) and (floating adj gate) and (self adj aligned)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:13
-	652	257/314.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:15
-	1580	257/316.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:21
-	355	257/316.ccls. and spacers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:40
-	99	257/317.ccls. and spacers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:42
-	43	257/318.ccls. and spacers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:44
-	81	257/319.ccls. and spacers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:47
-	68	257/320.ccls. and spacers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:49
-	170	257/321.ccls. and spacers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:52

-	53	257/322.cc	adj spacers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:53
-	1	(nonvolatile adj memory adj cell) and (contacting adj floating adj gate)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:55
-	16	(nonvolatile adj memory adj cell) and (contact adj floating adj gate)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 10:55
-	6	(nonvolatile adj memory adj cell) and (via adj floating adj gate)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 11:13
-	0	(nonvolatile adj memory adj cell) and (polysilicon adj sidewall adj spacer)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 11:14
-	180	polysilicon adj sidewall adj spacer		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 11:24
-	18	control adj gate adj sidewall adj spacer		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 11:22
-	859	polysilicon adj spacer		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 11:25
-	221	(polysilicon adj spacer) and (control adj gate)		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 09:52